Technology	tronic Co., Ltd					ificatio pprova
N5GSP-M84DDS-N000SA STANDARD RECTIFIER GPP CHIP				HF Pb RoH		
VOLTAGE: 1000 Volts		npers				
FEATURES  Glass Passivated Chip Junction Low Forward Voltage Drop For High Efficiency Low Leakage Current For High Reliability High Forward Surge Capability For High Reliab	y	1	<ul> <li>LED Dri</li> </ul>	Charger Power Supply	NS	
Mechanical Data						
Chip Drawing			Chip Dimensions			
		Symbol	1	ale	Tolerance	Unit
1	Chip Size	A	2.1	08	±0.050	mm
	Pad Size	В	1.4	-28	±0.050	mm
	Chip Thickness	С	0.2	.55	±0.020	mm
	Wafer Size		4	5	±0.10	in
В	water Size		12	27	±2.54	mm
	Chip Surface Coating					
	Top Metal Ni-Ni					
	Back Metal Ni-Ni					
	Back Metal Passivation	Ni-Ni Sipos+Glass	+LTO			
= B    = B			+LTO			
$\begin{array}{c c} A \\ \hline P+ \\ C \\ \hline N+ \\ \hline B \end{array}$	Passivation		+LTO			
$A \rightarrow P^+$ $C \qquad N^+$ $B \qquad Maximum Ratings (Ta=25^{\circ}C Unless Or C)$	Passivation			SP-M84DDS-N0	00SA	Unit
A P+ C N N B Maximum Ratings (Ta=25°C Unless Of Parameter Maximum Repetitive Peak Reverse Voltage	Passivation Passivation Dtherwise Specified) Test Conditions	Sipos+Glass Symbol V <sub>RRM</sub>		1000	00SA	V
A P P P P B Maximum Ratings (Ta=25°C Unless O Parameter Maximum Repetitive Peak Reverse Voltage Maximum Average Forward Rectified Current	Passivation Passivation Dtherwise Specified)	Sipos+Glass Symbol V <sub>RRM</sub> I <sub>F(AV)</sub>			00SA	
A P# P P P P P P P P P P P P P P P P P P	Passivation         Passivation         Otherwise Specified)         Test Conditions         @TC= 100 °C         8.3ms Single Half Sine-wave Superimposed On Rate Load	Sipos+Glass Symbol V <sub>RRM</sub> I <sub>F(AV)</sub>		1000 3	00SA	V A
A P# P P P P P P P P P P P P P P P P P P	Passivation         Passivation         Otherwise Specified)         Test Conditions         @TC= 100 °C         8.3ms Single Half Sine-wave Superimposed On Rate Load	Sipos+Glass Symbol V <sub>RRM</sub> I <sub>F(AV)</sub>	N50	1000 3 110		V A
A P C P B Maximum Ratings (Ta=25°C Unless O Parameter Maximum Repetitive Peak Reverse Voltage Maximum Average Forward Rectified Current Peak Forward Surge Current Electrical Characteristcs (Ta=25°C U	Passivation         Passivation         Otherwise Specified)         Test Conditions         @TC= 100 °C         8.3ms Single Half Sine-wave Superimposed On Rate Load	Sipos+Glass Symbol V <sub>RRM</sub> I <sub>F(AV)</sub>	N50	1000 3 110 SSP-M84DDS-N00	00SA	V A
A P+ C P+ N B Maximum Ratings (Ta=25°C Unless ( Parameter Maximum Repetitive Peak Reverse Voltage Maximum Average Forward Rectified Current Peak Forward Surge Current	Passivation Passivation Dtherwise Specified) Central Conditions Central C	Sipos+Glass Symbol VRRM I <sub>F(AV)</sub> I I <sub>FSM</sub>	N50	1000 3 110 SSP-M84DDS-N00 Typ.		V A A
A P P P P P P P P P P P P P	Passivation Passivation Dtherwise Specified) Conditions	Sipos+Glass Symbol VRRM I <sub>F(AV)</sub> I I <sub>FSM</sub>	N50	1000 3 110 SSP-M84DDS-N00	005A Max.	V A A
A P+ C P+ N B Maximum Ratings (Ta=25°C Unless of Parameter Maximum Average Forward Rectified Current Parameter	Passivation         Passivation         Otherwise Specified)         Image: Conditions         Image: Ima	Sipos+Glass Symbol V <sub>RRM</sub> I <sub>F(AV)</sub> I Symbol V <sub>F</sub>	N50	1000 3 110 SSP-M84DDS-N00 Typ. 0.84	00SA Max. 0.94	V A A Unit V
A C P P B Maximum Ratings (Ta=25°C Unless ( P P P B Maximum Repetitive Peak Reverse Voltage Maximum Average Forward Rectified Current eak Forward Surge Current eak Forward Surge Current Electrical Characteristcs (Ta=25°C U P P P P P P P P P P P P P	Passivation         Passivation         Otherwise Specified)         Image: Conditions	Sipos+Glass Symbol V <sub>RRM</sub> I <sub>F(AV)</sub> Symbol Symbol	N50	1000 3 110 3 3 58P-M84DDS-N00 Typ. 0.84 0.72	005A Max. 0.94 0.82	V A A Unit
A P A P A B Maximum Ratings (Ta=25°C Unless of Parameter Maximum Average Forward Rectified Current Peak Forward Surge Current Peak Forward Surge Current Parameter Instaneous Forward Voltage Per Diode (note1) Maximum DC Reverse Current At Rated DC Blocking Voltage (Note 1)	Passivation         Passivation         Dtherwise Specified)         Test Conditions         @TC=       100 °C         8.3ms Single Half Sine-wave Superimposed On Rate Load         Illog °C         8.3ms Single Half Sine-wave Superimposed On Rate Load         Illog °C         1       Test Conditions         Ta=25°C       I <sub>F</sub> =       3.0 A         Ta=25°C       V <sub>R</sub> = V <sub>RRM</sub> Ta=125°C         Ta=125°C       V <sub>R</sub> = 80%*V <sub>RRM</sub>	Sipos+Glass Symbol V <sub>RRM</sub> I <sub>F(AV)</sub> I Symbol V <sub>F</sub>	N50	1000 3 110 SSP-M84DDS-N00 Typ. 0.84 0.72 0.10	005A Max. 0.94 0.82 1.00	V A A Unit V
A C C C C C C C C C C C C C	Passivation         Passivation         Dtherwise Specified)         Test Conditions         @TC=       100 °C         8.3ms Single Half Sine-wave Superimposed On Rate Load         Illog °C         8.3ms Single Half Sine-wave Superimposed On Rate Load         Illog °C         1       Test Conditions         Ta=25°C       I <sub>F</sub> =       3.0 A         Ta=25°C       V <sub>R</sub> = V <sub>RRM</sub> Ta=125°C         Ta=125°C       V <sub>R</sub> = 80%*V <sub>RRM</sub>	Sipos+Glass Symbol V <sub>RRM</sub> I <sub>F(AV)</sub> Symbol V <sub>F</sub> I <sub>RRM</sub>	N50	1000 3 110 3 3 58P-M84DDS-N00 7yp. 0.84 0.72 0.10 50.00	005A Max. 0.94 0.82 1.00 100.00	V A A Unit V uA
$\begin{array}{c c} A \longrightarrow \\ \hline P + \end{array}$	Passivation         Passivation         Dtherwise Specified)         Test Conditions         @TC=       100 °C         8.3ms Single Half Sine-wave Superimposed On Rate Load         Illog °C         8.3ms Single Half Sine-wave Superimposed On Rate Load         Illog °C         1       Test Conditions         Ta=25°C       I <sub>F</sub> =       3.0 A         Ta=25°C       V <sub>R</sub> = V <sub>RRM</sub> Ta=125°C         Ta=125°C       V <sub>R</sub> = 80%*V <sub>RRM</sub>	Sipos+Glass Symbol V <sub>RRM</sub> I <sub>F(AV)</sub> I Symbol V <sub>F</sub>	N50	1000 3 110 3 3 3 3 110 3 3 5 9 - M84DDS-N00 50.00 3 5 9 - M84DDS-N00 5 9 - M84DDS-N00	005A Max. 0.94 0.82 1.00 100.00	V A A Unit V



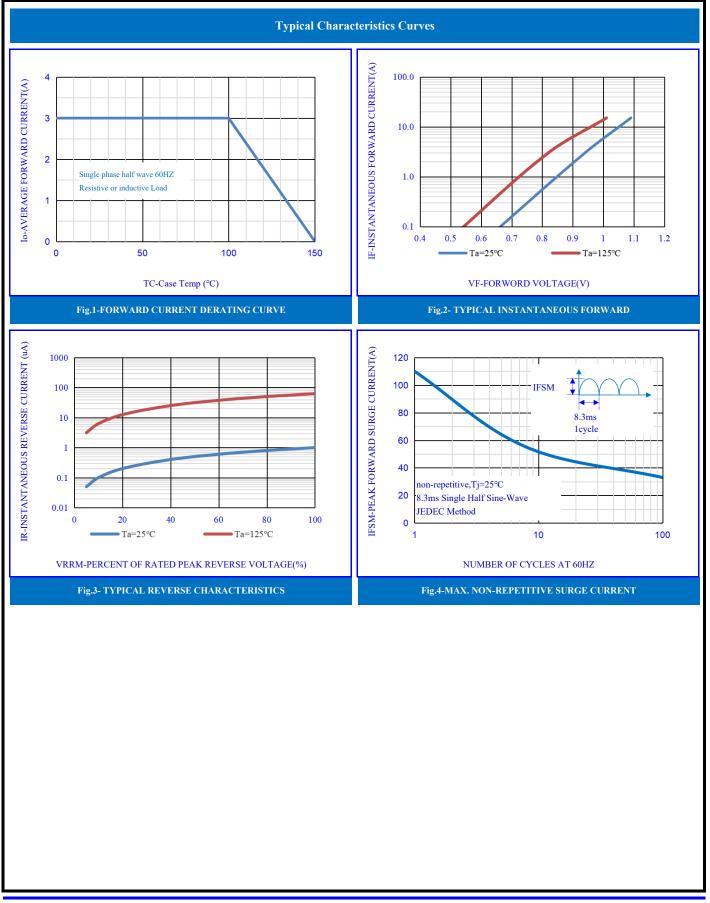
## N5GSP-M84DDS-N000SA

### STANDARD RECTIFIER GPP CHIP

*For Approval* (нг) (РФ) конс

en-free Pb-Frce COMPLIANT

Specification





## N5GSP-M84DDS-N000SA

# Specification For Approval

COMPLIANT

## STANDARD RECTIFIER GPP CHIP

## Disclaimer

- Reproducing and modifying informatiom of the document is prohibited without permission from niuhang Electronics Technology co., LTD
- Niuhang Electronics Technology co., LTD. reserves the rights to make changes of the content herein the document anytime without notification.
- Niuhang Electronics Technology co., LTD. disclaims any and all liability arising out of the application or use of any product including damages incidentally and consequentially occurred.
- Niuhang Electronics Technology co., LTD. does not assume any and all implied warranties, including warranties of fitness for particular purpose, non-infringement and merchantability.
- Applications shown on the herein document are examples of standard use and operation. Customers are responsible in comprehending the suitable use in particular applications.niuhang Electronics Technology co., LTD.makes no representation or warranty that such applications will be suitable for the specified use without further testing or modification.
- The products shown herein are not designed and authorized for equipments requiring high level of reliability or relating to human life and for any applications concerning life-saving or life-sustaining, such as medical instruments.transportation equipment, aerospae machinery et cetera. Customers usin or selling these products for use in such applications do so at their own rish and agree to fully indemnify niuhang Electronics Technology co., LTD for any damages resulting resulting from such improper use or sale.
- When the appearance of the product and chip size does not change, in order to product the customer. quality, change the internal structure and the production process Niuhang can not notify